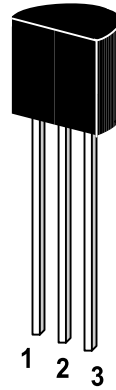


# ST 2N2907 / 2N2907A

PNP Silicon Epitaxial Planar Transistor  
for switching and AF amplifier applications.

The transistor is subdivided into one group according to its DC current gain. As complementary type the NPN transistor ST 2222 and ST 2222A are recommended.

On special request, these transistors can be manufactured in different pin configurations.



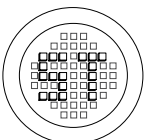
1. Emitter 2. Base 3. Collector

TO-92 Plastic Package  
Weight approx. 0.19g

Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

	Symbol	Value		Unit
		ST 2907	ST 2907A	
Collector Base Voltage	$-V_{\text{CBO}}$	60		V
Collector Emitter Voltage	$-V_{\text{CEO}}$	40	60	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5		V
Collector Current	$-I_{\text{C}}$	600		mA
Power Dissipation	$P_{\text{tot}}$	625		mW
Junction Temperature	$T_{\text{j}}$	150		$^\circ\text{C}$
Storage Temperature Range	$T_{\text{s}}$	-55 to +150		$^\circ\text{C}$

G S P FORM A IS AVAILABLE



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**РАДИОТЕХ**

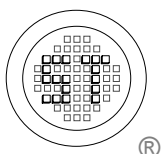
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# ST 2N2907 / 2N2907A

## Characteristics at $T_{amb}=25^{\circ}\text{C}$

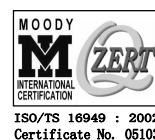
		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain						
at $-I_C=0.1\text{mA}$ , $-V_{CE}=10\text{V}$	ST 2907	$h_{FE}$	35	-	-	-
	ST 2907A	$h_{FE}$	75	-	-	-
at $-I_C=1\text{mA}$ , $-V_{CE}=10\text{V}$	ST 2907	$h_{FE}$	50	-	-	-
	ST 2907A	$h_{FE}$	100	-	-	-
at $-I_C=10\text{mA}$ , $-V_{CE}=10\text{V}$	ST 2907	$h_{FE}$	75	-	-	-
	ST 2907A	$h_{FE}$	100	-	-	-
at $-I_C=150\text{mA}$ , $-V_{CE}=10\text{V}$		$h_{FE}$	100	-	300	-
at $-I_C=500\text{mA}$ , $-V_{CE}=10\text{V}$	ST 2907	$h_{FE}$	30	-	-	-
	ST 2907A	$h_{FE}$	50	-	-	-
Collector Cutoff Current						
at $-V_{CE}=30\text{V}$		$-I_{CEX}$	-	-	50	nA
Collector Cutoff Current						
at $-V_{CB}=50\text{V}$	ST 2907	$-I_{CBO}$	-	-	20	nA
	ST 2907A	$-I_{CBO}$	-	-	10	nA
Collector Base Breakdown Voltage						
at $-I_C=10\mu\text{A}$		$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage						
at $-I_C=10\text{mA}$	ST 2907	$-V_{(BR)CEO}$	40	-	-	V
	ST 2907A	$-V_{(BR)CEO}$	60	-	-	V
Emitter Base Breakdown Voltage						
at $-I_E=10\mu\text{A}$		$-V_{(BR)EBO}$	5	-	-	V
Collector Saturation Voltage						
at $-I_C=150\text{mA}$ , $-I_B=15\text{mA}$		$-V_{CE(sat)}$	-	-	0.4	V
at $-I_C=500\text{mA}$ , $-I_B=50\text{mA}$		$-V_{CE(sat)}$	-	-	1.6	V
Base Saturation Voltage						
at $-I_C=150\text{mA}$ , $-I_B=15\text{mA}$		$-V_{BE(sat)}$	-	-	1.3	V
at $-I_C=500\text{mA}$ , $-I_B=50\text{mA}$		$-V_{BE(sat)}$	-	-	2.6	V
Gain Bandwidth Product						
at $-I_C=50\text{mA}$ , $-V_{CE}=20\text{V}$ , $f=100\text{MHz}$		$f_T$	200	-	-	MHz
Collector Output Capacitance						
at $-V_{CB}=10\text{V}$ , $f=1\text{MHz}$		$C_{ob}$	-	-	8	pF
Input Capacitance						
at $-V_{BE}=2\text{V}$ , $f=1\text{MHz}$		$C_{ib}$	-	-	30	pF

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**SEMTECH ELECTRONICS LTD.**

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002